ECEN325 Ref Sheet © Josh Wright April 23, 2017

Metric Prefixes

peta	P	10^{15}	1 000 000 000 000 000
tera	T	10^{12}	1 000 000 000 000
giga	G	10^{9}	1 000 000 000
mega	M	10^{6}	1 000 000
kilo	k	10^{3}	1 000
hecto	h	10^{2}	100
deca	da	10^{1}	10
one		10^{0}	1
deci	d	10^{-1}	0.1
centi	c	10^{-2}	0.01
milli	m	10^{-3}	0.001
micro	μ	10^{-6}	0.000 001
nano	n	10^{-9}	0.000 000 001
pico	p	10^{-12}	0.000 000 000 001
femto	f	10^{-15}	0.000 000 000 000 001

Ohm's Law $V = IR, \quad I = \frac{V}{R}, \quad R = \frac{V}{I}$

Battery Symbol

The side with the longer line is the positive side

Complex Numbers

- $z = x + iy = re^{i\theta} = r[\cos(\theta) + i\sin(\theta)]$
- $[r(\cos(\theta) + i\sin(\theta))]^n = r^n[\cos(n\theta) + i\sin(n\theta)]$
- $z^n = (re^{i\theta}) = r^n e^{in\theta}$
- $\frac{1}{i} = -i$
- $\sqrt[n]{z} = \sqrt[n]{r}e^{\frac{\theta}{n} + \frac{2k\pi}{n}}$ for $n \in N^*$ (ints ≥ 0)
- $e^{j\theta} = \cos(\theta) + j\sin(\theta)$ | $e^{-j\theta} = \cos(\theta) - j\sin(\theta)$
 $\cos(\theta) = \frac{1}{2}(e^{j\theta} + e^{-j\theta})$ | $\sin(\theta) = \frac{1}{2j}(e^{j\theta} - e^{-j\theta})$
- normalized: $sinc(t) = \frac{\sin(\pi t)}{\pi t}$
- $|\frac{a}{b}| = \frac{|a|}{|b|}$ $\qquad \angle\frac{a}{b} = \angle a - \angle b$

Trig

$\cos(2a) = \cos^2(a) - \sin^2(a) = 2\cos^2(a) - 1 = 1 - 2\sin^2(a)$

$\cos^2(a) + \sin^2(a) = 1$ | $\sin(2a) = 2\sin(a)\cos(a)$

$\cos^2(a) = \frac{1}{2}(1 + \cos(2a))$ | $\sin^2(a) = \frac{1}{2}(1 - \cos(2a))$

Voltage Division between two non-zero points

$V_{DD} \to R_1 \to V_1 \to R_2 \to V_{EE}$ (superposition)

$V_1 = V_{DD}\frac{R_2}{R_1+R_2} + V_{EE}\frac{R_1}{R_1+R_2}$

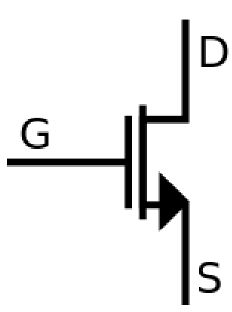
AC Resistors and Capacitors

$$R||\frac{1}{Cs} = \frac{R\frac{1}{Cs}}{R + \frac{1}{Cs}} = \frac{R}{RCs + 1}$$

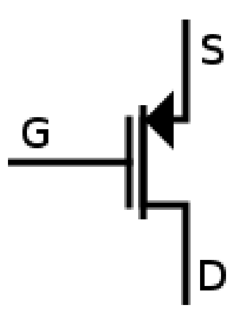
$$\frac{R}{R + \frac{1}{Cs}} = \frac{RCs}{RCs + 1} = \frac{s}{s + \frac{1}{RC}}$$

$$\frac{\frac{1}{Cs}}{R + \frac{1}{Cs}} = \frac{1}{RCs + 1}$$

MOS



NMOS



PMOS

MOS DC Biasing

- this is all for NMOS. PMOS is backward
- $\beta = k'_n(\frac{W}{L})$
- cutoff: $V_{GS} < V_{th}$
  - $I_D = 0$
- triode (linear): $V_{DS} < V_{GS} - V_{th}$
  - $I_D = k'_n\frac{W}{L}\left((V_{GS} - V_{th})V_{DS} - \frac{V_{DS}^2}{2}\right)$
- active (saturation): $V_{DS} > V_{GS} - V_{th}$
  - $I_D = \frac{k'_n}{2}\frac{W}{L}(V_{GS} - V_{th})^2$
  - overdrive voltage $V_{ov} = V_{GS} - V_{th}$
- to show it's active: show that $V_{DS} > V_{ov}$ or $V_{DS} > V_{GS} - V_{th}$

MOS Small Signal

	R_i	R_o	$\frac{V_o}{V_g}$
CS	$R_{G1}\|\|R_{G2}$	R_D	$-\frac{R_D\|\|R_L}{\frac{1}{g_m}+R_S}$
CG	$\frac{1}{g_m}$	R_D	$\frac{R_D\|\|R_L}{R_i}$
CD	$R_{G1}\|\|R_{G2}$	$\frac{1}{g_m}$	$\frac{R_L}{\frac{1}{g_m}+R_L}$

- $g_m = k'_n\frac{W}{L}(V_{GS} - V_t) = k'_p\frac{W}{L}(V_{SG} - V_t) = k'_n\frac{W}{L}(V_{ov})$
- CS: Common Source
- CG: Common Gate
- CD: Common Drain (buffer)
- apparently, when calculating the max gain of the frequency response, it is OK to just use the part of he equation that doesn't depend on s

MOS current mirrors

- where M1 is the transistor with base shorted to ground
- $\frac{I_{D1}}{I_{D2}} = \frac{(W/L)_1}{(W/L)_2}$
- $I_{D2} = \frac{(W/L)_2}{(W/L)_1}I_{D1}$

Bode Plots

- magnitude is plotted in dB: $|T(j\omega)|_{dB} = 20\log_{10}|T(j\omega)|$
- starts on y-axis at DC offset with slope 0
- just add together the bode plots of each individual pole, zero, and the DC offset
- poles always slope down, zeros slope up (applies for both magnitude and phase)
- dec=decade, e.g. from 10^0 to 10^1
- magnitude:
  - Pole/Zero at origin: constant slope $\pm 20db/dec$ for all ω; $0dB$ at $\omega = 10^0 = 1$
  - Pole/Zero at ω_0: 0 for $\omega < \omega_0$ slope $\pm 20\frac{db}{dec}$ after
  - Constant C: constant line at $20\log_{10}(|C|)$
- phase:
  - Pole at origin: constant $-\frac{\pi}{2}$ or $-90°$
  - Zero at origin: constant $+\frac{\pi}{2}$ or $+90°$
  - Pole/Zero at ω_0: 0 for $\omega < \frac{\omega_0}{10}$ slope linearly ($\pm 45°/dec$) until $10\omega_0$ 0 slope for $\omega > 10\omega_0$
  - Constant C: no effect (0 for all ω)
- Prof wants us to actually show the -3dB drop curve,

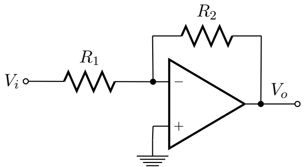
not just a straight intersection

- on the x-axis of the bode plot you need to plot frequency in Hz, so take $s = j\omega$ and divide by 2π

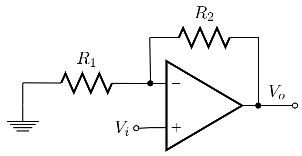
Solving systems with Op Amps

- only applies if the op-amp has feedback
- step 0: if the op amp is ideal, write out ideal properties:
  - $V_+ = V_-$
  - $I_- = 0, I_+ = 0$
  - $A \approx \infty$
- avoid doing KCL/KVL directly on the output node of the op amp
- ignore resistors from a point at $0V$ to ground

Op Amp Equations



Inverting Amplifier



Non-Inverting Amplifier

- ideal open-loop behavior: $(V_p - V_n) > 0 \rightarrow V_o = V_{DD}$ $(V_p - V_n) < 0 \rightarrow V_o = -V_{DD}$
- general form: $T(s) = \frac{K_0}{1+\frac{s}{\omega_0}}$
  - $T(0) = K_0$: DC offset. For these simple ones, it's equal to ideal response
  - $\omega_0 = \frac{\omega_t}{1+R_2/R_1}$
- inverting op amp:
  - ideal: $T(s) = \frac{V_o}{V_i} = -\frac{R_2}{R_1}$
  - non-ideal: $T(s) = \frac{V_o}{V_i} = \frac{-R_2/R_1}{1+\frac{1+R_2/R_1}{A(s)}} = \frac{-R_2/R_1}{1+\frac{s}{\left(\frac{\omega_t}{1+R_2/R_1}\right)}} = \frac{-R_2/R_1}{1+\frac{s}{\omega_0}}$
- non-inverting op-amp:
  - ideal: $T(s) = \frac{V_o}{V_i} = 1 + \frac{R_2}{R_1}$
  - non-ideal: $T(s) = \frac{V_o}{V_i} = \frac{1+R_2/R_1}{1+\frac{1+R_2/R_1}{A(s)}} = \frac{1+R_2/R_1}{1+\frac{s}{\left(\frac{\omega_t}{1+R_2/R_1}\right)}} = \frac{1+R_2/R_1}{1+\frac{s}{\omega_0}}$